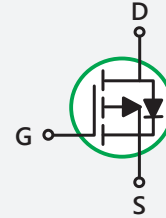
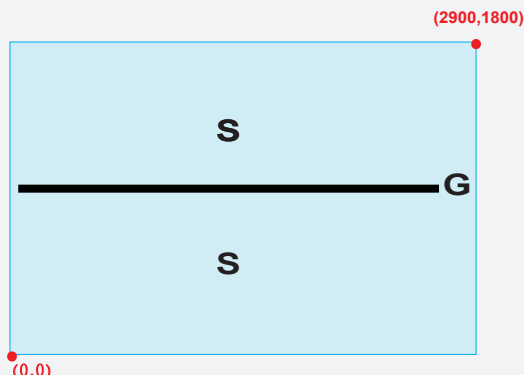


-60V P Channel Enhancement MOSFET Wafer Datasheet

FEATURES

- P-Channel,-60V
- Rds(ON)= 13mΩ (Typ.)@VGS=-10V
- Exceptional on-resistance and maximum DC current capability
high density cell design for extremely low RDS(ON)



Bonding Pad Information	Chip Information	
	Wafer Name	DC6M060P013M7
	Wafer Diameter	6 inches
	Wafer Thickness	7 mils
	Front-side Metallization	Al/Si/Cu (4um)
	Back-side Metallization	Ti/Ni/Ag
	Bonding Type	Gate: 1.5mil Cu x 1 Source: 40x6mil Al Ribbon x 2
	Die Size (without scribe line)	2900um x 1800um
	Scribe Line Width	60um
	Gate Pad Size	300um x 300um
	Gross Die	2.8K ea

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V , I _D =-250uA	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-48V , V _{GS} =0V			-1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V , V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1.0	-1.8	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V , I _D =-1A		13	16	m ohm
		V _{GS} =-4.5V , I _D =-1A		17	22	m ohm

Notes:

- 1.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- 2.RDS(ON) calculated by TO-220 Package Type.